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ATTORNEY DOCKET NO. CONFIRMATION NO. FILING DATE FIRST NAMED INVENTOR APPLICATION NO. 09/732,468 12/07/2000 Christopher Mark Bowles TI-24521 3187 12/20/2001 23494 7590 TEXAS INSTRUMENTS INCORPORATED EXAMINER P O BOX 655474, M/S 3999 PEREZ RAMOS, VANESSA DALLAS, TX 75265 ART UNIT PAPER NUMBER 1765 DATE MAILED: 12/20/2001

Please find below and/or attached an Office communication concerning this application or proceeding.

U.S. Patent and Trademark Office PTO-326 (Rev. 04-01) Art Unit: 1765

DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) do not apply to the examination of this application as the application being examined was not (1) filed on or after November 29, 2000, or (2) voluntarily published under 35 U.S.C. 122(b). Therefore, this application is examined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

2. Claims 1-2, 6-9, 13 and 17-18 are rejected under 35 U.S.C. 102(e) as being anticipated by Lin et al. (U.S. 6,057,207).

Lin discloses a method for forming a shallow trench isolation (col. 2, line 25) comprising: forming a plurality of isolation trenches in substrate, the trenches separating active areas (col. 2, lines 44-51); forming an insulating layer over the substrate, the insulating layer being silicon oxide (col. 2, line 53); filling the trenches and covering the active areas (col. 2, lines 52-55); forming a conformal barrier layer, which reads on Applicant's "planarization layer" on the insulating layer (col. 2, lines 57-61); removing the planarization layer and insulating layer (col. 2, lines 62-67 and col. 3, lines 1-8) down to a stop layer for the active areas (col. 7, lines 44-45). Furthermore, Lin discloses that the step of removing the planarization and insulation layers further comprise etching at a certain rate through the planarization layer and the insulation layer

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down to a certain depth, which reads on Applicant's "down to a CMP depth outward from the active areas" (col. 2, lines 62-67, col. 3, lines 1-2 and col. 6, lines 52-54) and then chemical mechanical polishing from there to the stop layer (col. 3, lines 3-8), said etch stop layer comprising silicon nitride (col. 7, lines 47-48) and being later removed (col. 7, lines 46-47).

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 4. Claims 3-5, 10-12, 14-16 and 19-20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lin et al. (U.S. 6,057,207), as applied to claims 1-2, 6-9, 13 and 17-18 above.

In regard to claims 3-5 and 14-16, Lin does not disclose that etching through the insulating and planarizing layers is done by an etch process that etches both layers at differing rates.

However, it is the Examiner's position that, since etching rate is a result-effective variable, its variation would have been obvious to one of ordinary skill in the art at the time of the invention, with the purpose of establishing the optimum process conditions.

In regard to claims 10 and 19, it is the Examiner's position that the use of a resist material would have been obvious to one of ordinary skill in the art at the time of the invention, since this is a widely-used material in the art.

In regard to claims 11 and 20, Lin does not disclose a preferred etching depth.

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However, it is the Examiner's position that, since depth is a result-effective variable, its

variation would have been obvious to one of ordinary skill in the art at the time of the invention,

with the purpose of establishing the optimum process conditions.

In regard to claim 12, the use of conformal layers would have been obvious to one of

ordinary skill in the art at the time of the invention, since this is a widely-used material in the art.

5. Any inquiry concerning this communication or earlier communications from the examiner

should be directed to Vanessa Perez-Ramos whose telephone number is 703-306-5510. The

examiner can normally be reached on Mon-Thurs 7:00am-5:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Benjamin Utech can be reached on 703-308-3836. The fax phone numbers for the

organization where this application or proceeding is assigned are 703-872-9310 for regular

communications and 703-872-9311 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is 703-306-5665.

Vanessa Perez-Ramos

Examiner

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VPR

December 15, 2001

BENJAMIN L. UTECH

SUPERVISORY PATENT EXAMINER

TECHNOLOGY CENTER 1700